

### INSTRUCTIONS

#### **FOR**

# SQUELCH TAIL ELIMINATOR BOARD 19A130001G1

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#### DESCRIPTION

The Squelch Tail Eliminator Board is required only in two-frequency transmit MASTR® II Remote Control Base Stations equipped with Channel Guard. The board circuitry holds either the F1 or F2 transmitter oscillator control leads at ground potential during the 160 millisecond DE-LAYED PTT period, preventing the selection of an alternate transmitter frequency before the DELAYED PTT is released.

### CIRCUIT ANALYSIS

When remote PTT is released, the DE-LAYED PTT lead A9 is grounded at the Channel Guard board for a period of 160 ms. Assume that the transmit F1 oscillator was selected for the transmission. The transmit frequency control lead A5 will be grounded, with Q1 and Q2 (F1 LEVEL INVERTERS) operated. Conduction of Q2 provides a low to pin 9 of NOR gate U1-C. Pin 10 at U1-C will also be low as the result of the output of U1-A. The resultant high output of U1-C at pin 8 is inverted to a low by U1-D and this low is applied to pin 6 of F1 DETECT GATE U1-B.

The ground on the DELAYED PTT lead A9 operates PTT LEVEL INVERTER transistors Q3

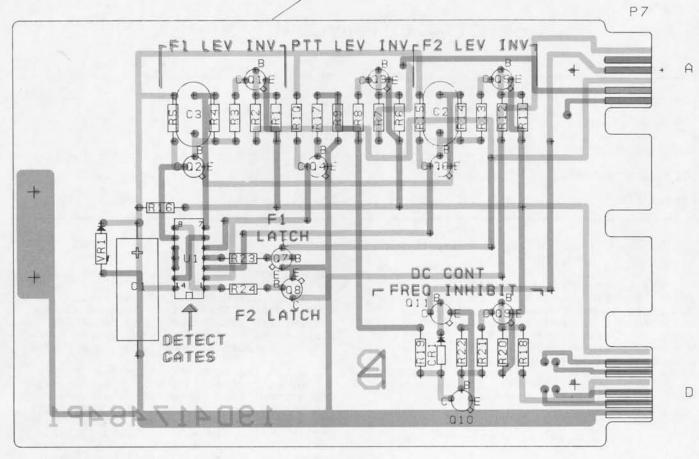
and Q4, applying a low to pin 5 of U1-B. The resultant high at pin 4 of U1-B operates F1 LATCH SWITCH Q7 and maintains the ground on the TRANSMIT F1 lead A5 during the DELAYED PTT period. The F2 LATCH circuit operates in the same manner when the F2 transmitter oscillator is selected.

In DC remote control systems, with a number of paralleled remote control units, the control line current will not instantly rise to +6 mA or +11 mA at the station. The station may thus attempt to key momentarily on the non-selected transmitter oscillator as the control current passes through the alternate line level. Gates U1-C, U1-D and the DC CONTROL FREQ. IN-HIBIT SWITCH are provided to avoid this momentary keying of the undesired frequency. Gate U1-C will not allow F1 to be latched if F2 is selected. Q11 prevents the DC Control Board from selecting F1 when the current decays through the +6 mA level.

When PTT is released at the DC remote control unit, the REMOTE PTT lead D4 goes high. Transistors Q9 and Q10 are turned off and diode CR1 is forward biased from the PTT LEVEL INVERTER. Q11 is thus turned on, grounding the DC FREQ. SELECT INHIBIT lead A4 to prevent the DC Control Board from selecting the alternate transmitter oscillator during the DELAYED PTT period.

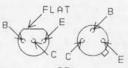
GENERAL ELECTRIC COMPANY • MOBILE COMMUNICATIONS DIVISION WORLD HEADQUARTERS • LYNCHBURG, VIRGINIA 24502 U.S.A.





(19D423279, Rev. 2) (19D417464, Sh. 2, Rev. 3) (19D417464, Sh. 3, Rev. 4)

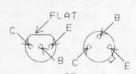
FOR 01.03.05.809



IN-LINE TRIANGULAR TOP VIEW

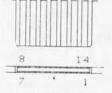
NOTE: LEAD ARRANGEMENT. AND NOT CASE SHAPE. IS DETERMINING FACTOR FOR LEAD IDENTIFICATION.

LEAG IDENTIFICATION FOR 02.04,06.07.08,010.&011



IN-LINE TRIANGULAR

NOTE: LEAD ARRANGEMENT, AND NOT CASE SHAPE, IS DETERMINING FACTOR FOR LEAD IDENTIFICATION

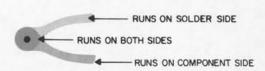


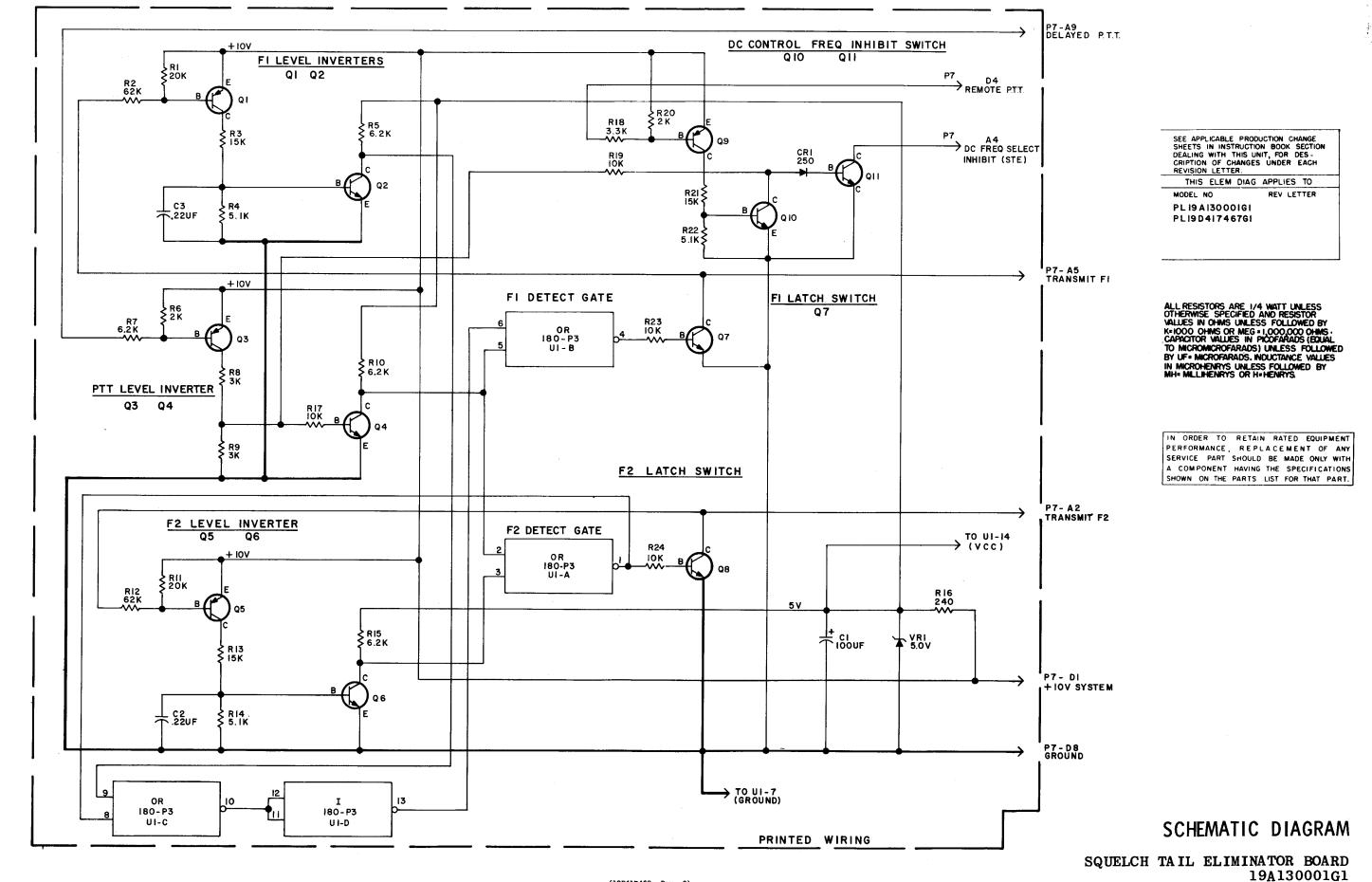
SOLDER SIDE TYP. NUMBERING OF CONTACT FINGERS.

DETAIL "A"

# OUTLINE DIAGRAM

SQUELCH TAIL ELIMINATOR BOARD 19A130001G1





LBI30716

## PARTS LIST

LBI-4881

#### SQUELCH TAIL ELIMINATOR BOARD 19A130001G1

	GE PART NO.	DESCRIPTION
	19 <b>B2</b> 19690G1	Handle assembly.
	19D417384P1	Panel.
		COMPONENT BOARD 19D417467G1
		CADACIMODS
C1	19A115680P7	Electrolytic: 100 µf +150% -10%, 15 VDCW; sim to Mallory Type TT.
C2 and C3	19A116080P109	Polyester: 0.22 µf ±10%, 50 VDCW.
		DIODES AND RECTIFIERS
CR1	19A115250P1	Silicon.
<b>P</b> 7		(Part of printed board 19D417464P1).
Q1	19A115768P1	Silicon, PNP; sim to Type 2N3702.
Q2	19A115910P1	Silicon, NPN; sim to Type 2N3904.
Q3	19Al15768Pl	Silicon, PNP; sim to Type 2N3702.
Q4	19A115910P1	Silicon, NPN; sim to Type 2N3904.
<b>Q</b> 5	19A115768Pl	Silicon, PNP; sim to Type 2N3702.
Q6 thru Q8	19A115910P1	Silicon, NPN; sim to Type 2N3904.
Q9	19A115768P1	Silicon, PNP; sim to Type 2N3702.
Q10 and Q11	19A115910P1	Silicon, NPN; sim to Type 2N3904.
R1	3R152P203J	Composition: 20,000 ohms $\pm 5\%$ , $1/4$ w.
R2	3R152P623J	Composition: 62,000 ohms ±5%, 1/4 w.
R3	3R152P153J	Composition: 15,000 ohms $\pm 5\%$ , $1/4$ w.
R4	3R152P512J	Composition: 5100 ohms $\pm 5\%$ , $1/4$ w.
15	3R152P622J	Composition: 6200 ohms ±5%, 1/4 w.
16	3R152P202J	Composition: 2000 ohms ±5%, 1/4 w.
17	3R152P622J	Composition: 6200 ohms ±5%, 1/4 w.
R8 and R9	3R152P302J	Composition: 3000 ohms ±5%, 1/4 w.
R10	3R152P622J	Composition: 6200 ohms ±5%, 1/4 w.
211	3R152P203J	Composition: 20,000 ohms $\pm 5\%$ , $1/4$ w.
112	3R152P623J	Composition: 62,000 ohms ±5%, 1/4 w.
113	3R152P153J	Composition: 15,000 ohms ±5%, 1/4 w.
114	3R152P512J	Composition: 5100 ohms $\pm 5\%$ , $1/4$ w.
215	3R152P622J	Composition: 6200 ohms ±5%, 1/4 w.
116	3R152P241J	Composition: 240 ohms ±5%, 1/4 w.
117	3R152P103J	Composition: 10,000 ohms $\pm 5\%$ , $1/4$ w.
	3R152P332J	Composition: 3300 ohms ±5%, 1/4 w.
R18	3R152P103J	Composition: $10,000$ ohms $\pm 5\%$ , $1/4$ w.
R18 R19	0.110271000	

	SYMBOL	GE PART NO.	DESCRIPTION
	R21 R22 R23 and R24	3R152P153J 3R152P512J 3R152P103J	Composition: 15,000 ohms ±5%, 1/4 w.  Composition: 5100 ohms ±5%, 1/4 w.  Composition: 10,000 ohms ±5%, 1/4 w.
	U1	19A116180P3	INTEGRATED CIRCUITS Digital, Quad 2-Input Nor Gate; sim to Texas Instrument Type SN7402N.
	VR1	<b>4</b> 036887 <b>P</b> 56	WOLTAGE REGULATOR Silicon, Zener.
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\*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES.